

-1-

BOX PCT

IN THE UNITED STATES DESIGNATED/ELECTED OFFICE
OF THE UNITED STATES PATENT AND TRADEMARK OFFICE
UNDER THE PATENT COOPERATION TREATY-CHAPTER II

11/24/00

5

AMENDMENT "A" PRIOR TO ACTION

APPLICANT(S): Gerald Deboy et al.

ATTORNEY DOCKET NO.: P00,0578

INTERNATIONAL APPLICATION NO.: PCT/DE98/03197

INTERNATIONAL FILING DATE: 02 November 1998

10 INVENTION: "HIGH VOLTAGE RESISTANT EDGE STRUCTURE
FOR SEMICONDUCTOR COMPONENTS"

Assistant Commissioner for Patents

Washington, D.C. 20231

Sir:

15 Applicants herewith amend the above-referenced PCT application, and
request entry of the Amendment prior to examination in the United States
National Examination Phase.

IN THE SPECIFICATION:

On page 1, cancel the title above line 3, and insert the following above line

20 3:

--TITLE

**HIGH VOLTAGE RESISTANT EDGE STRUCTURE FOR
SEMICONDUCTOR COMPONENTS**

25

BACKGROUND OF THE INVENTION--;

in line 3, after "The" insert --present--;

in line 4, cancel "according to the preamble of Patent Claim 1";

in line 8, cancel "the" substitute --a-- therefor;

in line 10, preceding "second" cancel "the" substitute --a-- therefor;